



POWRFET™
SILICON EPITAXIAL JUNCTION
N-CHANNEL FIELD EFFECT TRANSISTORS

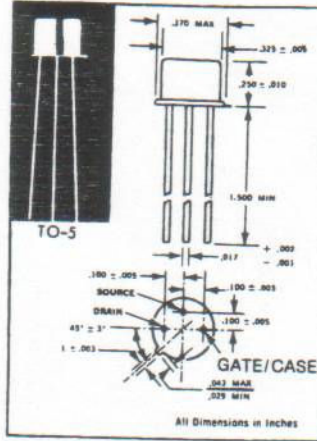
CP650
CP651
CP652
CP653

GEOMETRY 424

- LOW R_{DS} - 5 Ohms TYPICAL
- LOW C_{GD} - 20 pfd TYPICAL
- HIGH I_{DSS} - 0.5 Amp TYPICAL
- HIGH g_m - 150,000 μ mhos TYPICAL

ELECTRICAL DATA **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	CP650	CP651	CP652	CP653	UNITS
Drain to Source Voltage	BV_{DSO}	25	20	20	20	Volts
Drain to Gate Voltage	BV_{DGO}	25	20	20	20	Volts
Gate to Source Voltage	BV_{GSO}	-25	-20	-20	-20	Volts
Peak Drain Current	I_D	1.2	0.6	0.6	0.6	Amps
Power Dissipation 25°C Case	P_D	8.0	8.0	8.0	8.0	Watts
Derating Factor (slope)	DF	22	22	22	22	°C/W
Junction Temp. (Oper. & Store)	T_J		-65°C to +200°C			



ELECTRICAL CHARACTERISTICS: $T_{CASE} = 25^\circ C$ (UNLESS OTHERWISE STATED)

PARAMETERS AND CONDITIONS	SYMBOL	AMPLIFIERS						SWITCHES						UNITS
		CP650			CP651			CP652			CP653			
		Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
Gate Leakage Current $V_{GS} = -15V, V_{DS} = 0$	I_{GSS}	-	5.0	100	-	5.0	100	-	-	100	-	-	100	nA
Gate Leakage Current $V_{GS} = -15V, V_{DS} = 0, TC = 100^\circ C$	I_{GSS}	-	-	10	-	-	10	-	-	10	-	-	10	μA
Transconductance ¹ $V_{DS} = 15V, V_{GS} = 0$	g_m	0.1	0.15	0.25	0.075	0.1	0.2	-	0.1	-	-	0.06	-	mhos
Pinch-Off Voltage $V_{DS} = 5V, I_{DS} = 1.0mA/3nA^*$	V_{PO}	2.0	5.0	10	2.0	5.0	10	2.0*	5.0*	10*	2.0*	5.0*	10*	Volts
On Resistance $I_{DS} = 10mA, V_{GS} = 0$	R_{DS}	-	4.0	-	-	7.0	-	-	4.0	6.0	-	7.0	12	Ohms
Gate to Source Cap. $V_{GS} = -20V$	C_{GS}	-	20	25	-	20	25	-	20	25	-	20	25	pfd
Gate to Drain Cap. $V_{GD} = -20V$	C_{GD}	-	20	25	-	20	25	-	20	25	-	20	25	pfd
Drain Current ¹ $V_{DS} = 15V, V_{GS} = 0$	I_{DSS}	0.3	0.6	1.2	0.1	0.3	0.5	0.1	-	-	0.06	-	-	Amps
Gain-Bandwidth Product $V_{DS} = 15V, V_{GS} = 0$	F_t	-	1.0	-	-	1.0	-	-	1.0	-	-	1.0	-	GHz

¹ Pulse Measurement 1% Duty Cycle 10 mS Max.

™ TRADEMARK OF CRYSTALONICS, INC.

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